

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a gate electrode over a substrate;

~~sequentially forming a gate insulating film over the gate electrode and an initial semiconductor film on an insulating surface having gate lines formed thereon such that they are stacked without being exposed to the atmosphere;~~

~~crystallizing said initial semiconductor film by irradiating it with infrared light or ultraviolet light to form a crystalline semiconductor film and an oxide film simultaneously;~~
and

forming a semiconductor film over the gate insulating film;

covering a region to become a channel formation region of said ~~crystalline~~ semiconductor film with a first mask and doping a region to become a source region or drain region of said ~~crystalline~~ semiconductor film with a trivalent or pentavalent impurity element through said oxide film; and

covering a portion of the first mask and either a portion of the source region or a portion of the drain region with a second mask.

2. (Cancel).

3. (Currently Amended) A method according to claim 1 wherein contaminants on ~~the~~ a surface of the substrate on which said ~~initial~~ semiconductor film is to be formed are reduced using active hydrogen or a hydride.

4. (Original) A method according to claim 1 further comprising the step of forming a multi-layer film including a silicon nitride film as any of the layers as said gate insulating film.

5. (Original) A method according to claim 1 further comprising the step of forming a multi-layer film including benzocyclobutene as a part of said gate insulating film.

6. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a gate electrode over a substrate;

sequentially forming a gate insulating film over the gate electrode, an initial semiconductor film and an insulating film on an insulating surface having gate lines formed thereon such that they are stacked without being exposed to the atmosphere;

forming a semiconductor film over the gate insulating film;

forming an insulating film over the semiconductor film;

crystallizing said ~~initial~~ semiconductor film by irradiating it with infrared light or ultraviolet light through said insulating film to form a crystalline semiconductor film; and

covering a region to become a channel formation region of said crystalline semiconductor film with a first mask and doping a region to become a source region or drain region of said crystalline semiconductor film with a trivalent or pentavalent impurity element through said ~~oxide film~~ insulating film[[.]];

covering a portion of the first mask and either a portion of the source region or a portion of the drain region with a second mask; and

forming an interlayer insulating film over the first mask and the second mask.

7. (Currently Amended) A method for manufacturing a semiconductor device according to claim 6 wherein said gate insulating film, said initial semiconductor film and said ~~protective film~~ insulating film are formed using different chambers.

8. (Currently Amended) A method for manufacturing a semiconductor device according to claim 6 wherein said gate insulating film, said ~~initial~~ semiconductor film and said ~~protective film~~ insulating film are formed using the same chamber.

9. (Currently Amended) A method for manufacturing a semiconductor device according to claim 6 wherein said gate insulating film and said ~~protective film~~ insulating film are formed using a first chamber and wherein said ~~initial~~ semiconductor film is formed using a second chamber.

10. (Currently Amended) A method according to claim 6 further comprising the step of retaining a catalytic element for promoting the crystallization of silicon in contact with the surface of said ~~initial~~ semiconductor film or within said film after said step of forming the gate insulating film and the ~~initial~~ semiconductor film.

11. (Currently Amended) A method according to claim 6 wherein contaminants on ~~the~~ a surface of the substrate on which said initial semiconductor film is to be formed are reduced using active hydrogen or a hydride.

12. (Original) A method according to claim 6 further comprising the step of forming a multi-layer film including a silicon nitride film as any of the layers as said gate insulating film.

13. (Original) A method according to claim 6 further comprising the step of forming a multi-layer film including benzocyclobutene as a part of said gate insulating film.

14. (New) A method according to claim 1, wherein the second mask includes a material selected from a group consisting of a positive type photosensitive organic material or negative type photosensitive organic material, organic resin, a silicon oxide, a silicon nitride and silicon nitride oxide.

15. (New) A method according to claim 6, wherein the second mask includes a material selected from a group consisting of a positive type photosensitive organic material or negative type photosensitive organic material, organic resin, a silicon oxide, a silicon nitride and silicon nitride oxide.

16. (New) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a substrate;

covering a portion of a channel formation region of the semiconductor film and either a portion of a region to become a source region or a portion of a region to become a drain region of the semiconductor film with a mask;

doping the region to become the source region or the region to become the drain region of the semiconductor film with a trivalent or pentavalent impurity element; and

forming an interlayer insulating film over the mask.

17. (New) A method according to claim 16, further comprising the step of forming an insulating film over the semiconductor film.

18. (New) A method according to claim 16, wherein the mask includes a material selected from a group consisting of a positive type photosensitive organic material or negative type photosensitive organic material, organic resin, a silicon oxide, a silicon nitride and silicon nitride oxide.